

AMENDMENTS TO THE CLAIMS

Claim 1. (Original) A chemical-amplification type silicone-based positive-working resist composition characterized in that, in a chemical-amplification type positive-working resist composition containing (A) an alkali-soluble resin and (B) a photoacid-generating agent,
 a ladder-type silicone copolymer containing (a₁) (hydroxyphenylalkyl)sil-sesquioxane units, (a₂) (alkoxyphenylalkyl)sil-sesquioxane units and (a₃) alkyl- or phenylsil-sesquioxane units is used as the (A) alkali-soluble resin.

Claim 2. (Original) The chemical-amplification type silicone-based positive-working resist composition described in Claim 1 in which the component (A) is a ladder-type silicone copolymer consisting of 10-70% by moles of the units (a₁), 5-50% by moles of the units (a₂) and 10-60% by moles of the units (a₃).

Claim 3. (Currently Amended) The chemical-amplification type silicone-based positive-working resist composition described in Claim 1 ~~or 2~~ in which the proportion of the units (a₂) is so adjusted that the dissolving rate in alkali be from 0.05 to 50 nm/s.

Claim 4. (Currently Amended) The chemical-amplification type silicone-based positive-working resist composition described in Claim 1, ~~2 or 3~~ in which the component (B) is an onium salt or a diazomethane compound.

Claim 5. (Currently Amended) The chemical-amplification type silicone-based positive-working resist composition described in ~~either one of Claims 1 to 4~~ Claim 1 in which, in addition to the component (A) and component (B), a phenolic compound of which the phenolic hydroxyl group is protected by an acid-dissociable group or a carboxylic compound of which the carboxylic group is protected by an acid-dissociable group is compounded as a dissolution inhibitor (C), in a proportion of 0.5-40 parts by mass per 100 parts by mass of the component (A).

Claim 6. (Currently Amended) The chemical-amplification type silicone-based positive-working resist composition described in ~~either one of Claims 1 to 5~~ Claim 1 in which, in addition to the component (A) and component (B) or the component (A), component (B) and component (C), an amine and/or an organic acid are/is

compounded as a quencher (D) in a proportion of 0.01-5 parts by mass per 100 parts by mass of the component (A).

Claim 7. (Currently Amended) A bilayered resist material characterized in that an organic layer is provided on a substrate and a layer of the chemical-amplification type silicone-based positive-working resist composition described in ~~either one of Claims 1 to 6~~ Claim 1 is formed thereon.

Claim 8. (Original) The bilayered resist material described in Claim 7 in which the organic layer is a layer of a novolak resin or a layer of a novolak resin containing a 1,2-naphthoquinonediazido group.

Claim 9. (Currently Amended) The bilayered resist material described in Claim 7 ~~or 8~~ in which the organic layer has a thickness of 200-800 nm and the layer of the chemical-amplification type silicone-based positive-working resist composition has a thickness of 50-200 nm.

Claim 10. (Original) A ladder-type silicone copolymer which contains (hydroxyphenylalkyl)silsesquioxane units, (alkoxyphenylalkyl)silsesquioxane units and phenylsilsesquioxane units.

Claim 11. (Original) The ladder-type silicone copolymer described in Claim 10 which consists of 10-70% by moles of the (hydroxyphenylalkyl)silsesquioxane units, 5-50% by moles of the (alkoxyphenylalkyl)silsesquioxane units and 10-60% by moles of the phenylsilsesquioxane units.

Claim 12. (Currently Amended) The ladder-type silicone copolymer described in Claim 10 ~~or 11~~ of which the dissolving rate in alkali is in the range of 0.05-50 nm/s.

Claim 13. (Original) The ladder-type silicone copolymer described in Claim 10 of which the mass-average molecular weight is in the range of 1500-30000.

Claim 14. (Original) The ladder-type silicone copolymer described in Claim 10 of which the molecular weight dispersion is in the range of 1.0-5.0.

Claim 15. (Currently Amended) A method of forming a patterned resist film on a

substrate which comprises a step of selectively exposing the bilayered resist material described in ~~either one of Claims 7 to 9~~ Claim 7 to actinic rays, and a step of dissolving away the portion of the resist film solubilized by the light-exposure with an aqueous alkali solution.